

### **REMARKS**

This paper is in response to the Office Action mailed on August 11, 2004.

Claims 60, 62, 64-82, 84-87 are amended, claims 63 and 83 are canceled without prejudice or disclaimer, and claims 88-90 are added; as a result, claims 60-62, 64-82, and 84-90 are now pending in this application.

Claims 62, 64, 65, 67-73, 75-79, 81, 84, 86-87 are amended for clarity. The amendments are believed to not narrow the claims and may, in fact, be broadening amendments.

#### **§112 Rejection of the Claims**

Claims 62, 63, 83, and 87 were rejected under 35 USC § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which Applicant regards as the invention. The Office Action also indicates that claims 64-82 and 84-86 are also vague as to whether specific materials are required to be used in the claims method.

Applicant respectfully traverses and asserts that these claims meet the requirements of §112, second paragraph. Applicant believes these claims are now in condition for allowance. Applicant requests that the rejection be reconsidered and withdrawn.

#### **§102 Rejection of the Claims**

Claims 60-87 were rejected under 35 USC § 102(b) as being anticipated by Sandhu et al. (U.S. Patent No. 5,335,138). Applicant respectfully traverses because a prima facie case of anticipation has not been made.

Independent claim 61 recites, among other things, “forming an inhibiting layer abutting the second conductive layer, wherein the inhibiting layer inhibits formation of an undesired oxidation compound so as to enhance an ohmic contact” and “forming a diffusion barrier layer abutting the inhibiting layer”. Applicant is unable to find in Sandhu et al. “forming an inhibiting layer abutting the second conductive layer, wherein the inhibiting layer inhibits formation of an undesired oxidation compound so as to enhance an ohmic contact” and “forming a diffusion barrier layer abutting the inhibiting layer”. Accordingly, Applicant requests that the rejection of claim 61 be reconsidered and withdrawn and that claim 61 and its dependent claims be allowed.

Independent claim 66 recites, among other things, “forming an inhibiting layer abutting the second conductive layer, wherein the inhibiting layer inhibits formation of an undesired oxidation compound so as to enhance an ohmic contact” and “forming a diffusion barrier layer abutting the inhibiting layer”. Applicant is unable to find in Sandhu et al. “forming an inhibiting layer abutting the second conductive layer, wherein the inhibiting layer inhibits formation of an undesired oxidation compound so as to enhance an ohmic contact” and “forming a diffusion barrier layer abutting the inhibiting layer”. Accordingly, Applicant requests that the rejection of claim 66 be reconsidered and withdrawn and that claim 66 and its dependent claims be allowed.

Independent claim 74 recites, among other things, “forming an inhibiting layer abutting the second conductive layer” and “forming a diffusion barrier layer abutting the inhibiting layer”. Applicant is unable to find in Sandhu et al. “forming an inhibiting layer abutting the second conductive layer” and “forming a diffusion barrier layer abutting the inhibiting layer”. Accordingly, Applicant requests that the rejection of claim 74 be reconsidered and withdrawn and that claim 74 and its dependent claims be allowed.

Independent claim 80 recites, among other things, “forming an inhibiting layer abutting the second conductive layer” and “forming a metallization layer abutting the inhibiting layer, wherein the metallization layer comprises a representative metal, and wherein forming the metallization layer further includes forming a diffusion barrier abutting the inhibiting layer”. Applicant is unable to find in Sandhu et al. “forming an inhibiting layer abutting the second conductive layer” and “forming a metallization layer abutting the inhibiting layer, wherein the metallization layer comprises a representative metal, and wherein forming the metallization layer further includes forming a diffusion barrier abutting the inhibiting layer”. Accordingly, Applicant requests that the rejection of claim 80 be reconsidered and withdrawn and that claim 80 and its dependent claims be allowed.

Independent claim 85 recites, among other things, “forming a second insulation layer abutting the first conductive layer and the ohmic contact”, “forming an inhibiting layer abutting the second conductive layer” and “forming a metallization layer, wherein the metallization layer comprises a representative metal, wherein the representative metal includes aluminum, and wherein forming the metallization layer includes forming a diffusion barrier abutting the inhibiting layer”. Applicant is unable to find in Sandhu et al. “forming a second insulation layer

abutting the first conductive layer and the ohmic contact”, “forming an inhibiting layer abutting the second conductive layer” and “forming a metallization layer, wherein the metallization layer comprises a representative metal, wherein the representative metal includes aluminum, and wherein forming the metallization layer includes forming a diffusion barrier abutting the inhibiting layer”. Accordingly, Applicant requests that the rejection of claim 85 be reconsidered and withdrawn and that claim 85 and its dependent claims be allowed.

### **New Claims**

New claims 88-90 introduce no new matter. Applicant requests consideration and allowance of new claims 88-90.

CONCLUSION

Applicant respectfully submits that the claims are in condition for allowance, and notification to that effect is earnestly requested. The Examiner is invited to telephone Applicant's representative at (612) 373-6969 to facilitate prosecution of this application.

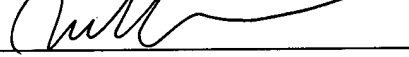
If necessary, please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

Respectfully submitted,

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Date 9 November 2004 By   
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 9 day of November, 2004.

Name

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Signature

